

RESPONSE UNDER 37 C.F.R. § 1.116
U.S. Appln. No. 09/649,013

Claims 2-12 and 19-21 are pending in the present application. The Examiner maintains all the rejections previously of record. The Advisory Action also includes a lengthy explanation of why the rejections are being maintained. However, some of the Applicant's arguments of record remain unrebutted by the Examiner. For example, the argument for claim 2 is unrebutted. The claims should be allowed absent an explanation in rebuttal.

The documents submitted herewith raise no new issues and should be entered as a matter of course. The documents show the relationship of prior JP documents and their corresponding U.S. counterparts described by the amended specification.

Applicant submits this Response to demonstrate the equivalents of the U.S. Patent and JP documents with regard to the incorporation by reference and Section 112 issues. The U.S. documents submitted herewith are each related to resist materials and correspond to JP references, also corresponding to resist materials previously described in the disclosure. Applicant would also submit that the Examiner's reference to JP 2002-20224 appears to be in error since it was a 2000 JP document (20224) submitted with the prior response.

Applicant further submits that Taguchi (JP 4-4335620) discusses electrode line widths outside the claimed range of claim 12.

With regard to the Examiner's criticism of the teachings of JP 7-114188, Applicant submits the translation of paragraphs [008] and [024]-[026] indicating the applicability of composition for resist materials.

In view of the above, Applicant submits that claims 2-12 and 19-21 are in condition for allowance. Therefore it is respectfully requested that the subject application be passed to issue at

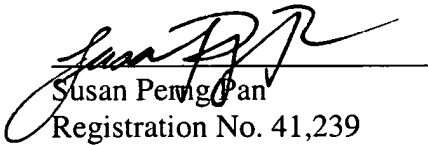
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the earliest possible time. The Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

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23373

CUSTOMER NUMBER

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7-114188

[0008] R1, R2, R3, and R4 among [formula A methyl group, n-propyl group, The substitution or the non-replaced aliphatic hydrocarbon machine like n-butyl, n-h xyl machine, a ph nylmethyl machine, a truffe RUORO propyl group, and a nona fluoro h xyl machine, it is the basis chosen respectively independently of the group which consists of substitution like p-tolyl group, a biphenyl machine, an aromatic-hydrocarbon machine like a phenyl group and a cyclohexyl machine, and a methyl cyclohexyl machine, or a non-replaced alioyolic hydrocarbon machine, and m and n are integers] The photopolymer constituent which comes out and contains the polysilane, the optical radical generating agent, and oxidizer of the structure shown is offered, and the above-mentioned purpose is attained by that.

[0024] An example of the process which forms a thin film pattern is shown in (a) - (d) of drawing 1. the layered product 104 for pattern thin film formation which consists of above substrates 101 and photosensitive layers 102 is first, like [as shown in drawing 1 (a)] a mercury-vapor lamp — according to a pattern, it irradiates using ultraviolet or the visible light source. Usually, irradiation of the light 110 is performed through ultraviolet or the pattern mask 103 piled up on the layered product 104 for thin film formation.

[0025] The light source used by this invention has the wavelength which an optical radical generating agent or coloring matter exposes. This irradiation is preferably performed with the quantity of light of per [0.2] micrometer in thlokness of a photosensitive layer — 5 J/cm².

[0026] Si-Si combination which exists in a photosensitive layer is cut by optical irradiation, and Si-OH (silanol group) generates it. Therefore, the latent image which has a silanol group according to a pattern is formed in the irradiated layered product for thin film formation.